

PRODUCT PROFILE

2SA1072, 2SA1072A, 2SA1073

Silicon High Speed Power Transistor

DESCRIPTION

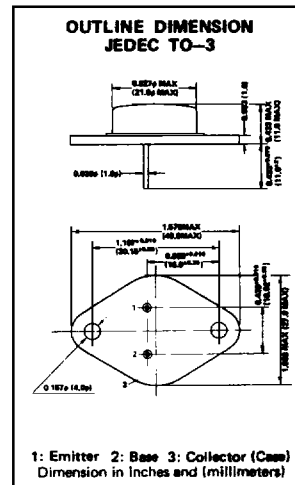
The 2SA1072/2SA1072A/2SA1073 are silicon PNP general purpose, high power switching transistors fabricated with Fujitsu's unique Ring Emitter Transistor (RET) technology. RET devices are constructed with multiple emitters connected through diffused ballast resistors which provide uniform current density. This structure permits the design of high power transistors with exceptional switching characteristics and frequency response in high current applications.

The 2SA1072/2SA1072A/2SA1073 are especially well-suited for high frequency power amplifiers, audio power amplifiers, switching regulators and DC-DC converters. NPN complements, 2SC2522/2SC2522A/2SC2523, are available.

- High $f_T = 60$ MHz (typ)
- Excellent safe operating area
- Ultra fast switching speed
- Improved reverse second-breakdown capability

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value			Unit
		2SA1072	2SA1072A	2SA1073	
Collector to Base Voltage	V_{CBO}	120	150	160	V
Emitter to Base Voltage	V_{EBO}	7	7	7	V
Collector to Emitter Voltage	V_{CEO}	120	150	160	V
Collector Current	I_C	12	12	12	A
Collector Power Dissipation ($T_C = 25^\circ\text{C}$)	P_C	120	120	120	W
Junction Temperature	T_J	+150			$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150			$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$)

Parameter	Symbol	Test Conditions	Limits						Unit
			2SA1072/2SA1072A			2SA1073			
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Collector Cutoff Current	I_{CBO}	$V_{CB} = 120\text{V}/160\text{V}, I_E = 0$	—	—	50/-	—	—	-/50	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 7\text{V}, I_C = 0$	—	—	50	—	—	50	μA
Collector Cutoff Current	I_{CEO}	$V_{CE} = 120\text{V}/160\text{V}, R_{BE} = \infty$	—	—	1/-	—	—	-/1	mA
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 50\mu\text{A}, I_E = 0$	120	—	—	160	—	—	V
			150*	—	—	—	—	—	V
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 50\mu\text{A}, I_C = 0$	7	—	—	7	—	—	V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, R_{BE} = \infty$	120	—	—	160	—	—	V
			150*	—	—	—	—	—	V
DC Current Gain	h_{FE1}	$V_{CE} = 5\text{V}, I_C = 1\text{A}^*$	60	—	200	60	—	200	—
DC Current Gain	h_{FE2}	$V_{CE} = 5\text{V}, I_C = 7\text{A}^*$	40	—	—	40	—	—	—
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 5\text{A}, I_B = 0.5\text{A}^*$	—	0.9	1.8	—	0.9	1.8	V
Base to Emitter Voltage	V_{BE}	$V_{CE} = 5\text{A}, I_C = 5\text{A}^*$	—	1.25	1.7	—	1.25	1.7	V
Gain-Bandwidth Product	f_T	$V_{CE} = 10\text{V}, I_C = 1\text{A}, f = 10\text{MHz}$	45	60	—	45	60	—	MHz
Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$	—	300	470	—	300	470	pF
Rise Time	t_r	$I_C = 7.5\text{A}, R_L = 4\Omega$ $I_{B1} = -I_{B2} = 0.75\text{A}$	—	0.15	—	—	0.15	—	μs
Storage Time	t_{stg}		—	0.5	—	—	0.5	—	μs
Fall Time	t_f		—	0.11	—	—	0.11	—	μs

* Pulsed; Pulse width $\leq 300\mu\text{s}$; Duty Cycle $\leq 6\%$
† For 2SA1072A only

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